

TRIACS

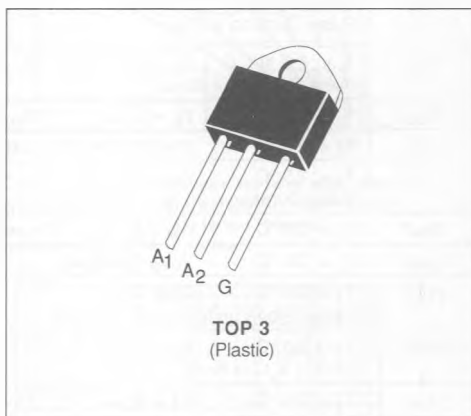
- GLASS PASSIVATED CHIP
- I_{GT} SPECIFIED IN FOUR QUADRANTS

DESCRIPTION

This new design of plastic uninsulated power triacs offers maximum efficiency with maximum ease of mounting.

ADVANTAGES

- NO TAPPING REQUIRED FOR FIXING
- EXCELLENT THERMAL IMPEDANCE AND HIGH RELIABILITY CONSTRUCTION



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
$I_{T(RMS)}$	RMS on-state Current (360° conduction angle)	$T_C = 90\text{ }^{\circ}\text{C}$	30	A
I_{TSM}	Non Repetitive Surge Peak on-state Current (T_j initial = 25 °C - Half sine wave)	$t = 8.3\text{ ms}$	260	A
		$t = 10\text{ ms}$	250	
I^2t	I^2t Value for Fusing	$t = 10\text{ ms}$	312.5	A ² s
di/dt	Critical Rate of Rise of on-state Current (1)	Repetitive $F = 50\text{ Hz}$	10	A/ μ s
		Non Repetitive	50	
T_{sig} T_j	Storage and Operating Junction Temperature Range		- 40 to 125 - 40 to 125	$^{\circ}\text{C}$ $^{\circ}\text{C}$

Symbol	Parameter	BTB 26-					Unit
		200A	400A	600A	700A	800A	
V_{DRM}	Repetitive Peak off-state Voltage (2)	200	400	600	700	800	V

(1) $I_G = 1.5\text{ A}$ $di/dt = 1\text{ A}/\mu\text{s}$

(2) $T_j = 125\text{ }^{\circ}\text{C}$.

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-a)}$	Junction to Ambient	50	$^{\circ}\text{C}/\text{W}$
$R_{th(c-h)}$	Contact (case-heatsink) with Grease	0.2	$^{\circ}\text{C}/\text{W}$
$R_{th(j-c)}\text{ DC}$	Junction to Case for DC	1.2	$^{\circ}\text{C}/\text{W}$
$R_{th(j-c)}\text{ AC}$	Junction to Case for 360 ° Conduction Angle ($F = 50\text{ Hz}$)	0.9	$^{\circ}\text{C}/\text{W}$

GATE CHARACTERISTICS (maximum values)

$P_{GM} = 40\text{ W}$ ($t_p = 10\text{ }\mu\text{s}$) $I_{GM} = 6\text{ A}$ ($t_p = 10\text{ }\mu\text{s}$)
 $P_{G(AV)} = 1\text{ W}$ $V_{GM} = 16\text{ V}$ ($t_p = 10\text{ }\mu\text{s}$)

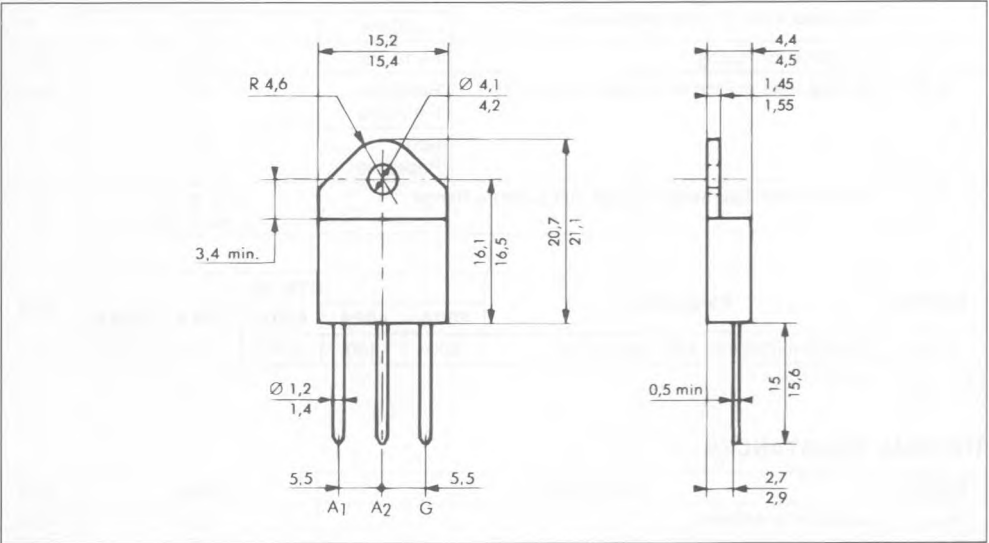
ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions			Quadrants	Min.	Typ.	Max.	Unit
I_{GT}	$T_j = 25\text{ }^\circ\text{C}$ Pulse Duration $> 20\text{ }\mu\text{s}$	$V_D = 12\text{ V}$	$R_L = 33\text{ }\Omega$	I-II-III	1		100	mA
				IV	1		150	
V_{GT}	$T_j = 25\text{ }^\circ\text{C}$ Pulse Duration $> 20\text{ }\mu\text{s}$	$V_D = 12\text{ V}$	$R_L = 33\text{ }\Omega$	I-II-III-IV			1.5	V
V_{GD}	$T_j = 125\text{ }^\circ\text{C}$	$V_D = V_{DRM}$	$R_L = 3.3\text{ k}\Omega$	I-II-III-IV	0.2			V
I_{H^*}	$T_j = 25\text{ }^\circ\text{C}$	$I_T = 500\text{ mA}$	Gate Open			30	100	mA
I_L	$T_j = 25\text{ }^\circ\text{C}$ Pulse Duration $> 20\text{ }\mu\text{s}$	$V_D = 12\text{ V}$	$I_G = 300\text{ mA}$	I-II-III-IV			150	mA
V_{TM^*}	$T_j = 25\text{ }^\circ\text{C}$	$I_{TM} = 35\text{ A}$	$t_p = 10\text{ ms}$				1.7	V
I_{DRM^*}	$T_j = 125\text{ }^\circ\text{C}$	V_{DRM} Specified				1.5	6	mA
dv/dt^*	$T_j = 125\text{ }^\circ\text{C}$	Gate Open	Linear Slope up to $V_D = 67\text{ }\% V_{DRM}$		250			V/ μs
$(dv/dt)_c^*$	$T_C = 90\text{ }^\circ\text{C}$ $(di/dt)_c = 13.3\text{ A/ms}$	$V_D = V_{DRM}$	$I_T = 35\text{ A}$		10			V/ μs
t_{g1}	$T_j = 25\text{ }^\circ\text{C}$ $I_G = 1\text{ A}$	$V_D = V_{DRM}$ $di_G/dt = 10\text{ A}/\mu\text{s}$	$I_T = 35\text{ A}$	I-II-III-IV		2.5		μs

* For either polarity of electrode A_2 voltage with reference to electrode A_1 .

PACKAGE MECHANICAL DATA

TOP 3 Plastic



Cooling method : by conduction (method C)
Marking : type number
Weight : 5 g

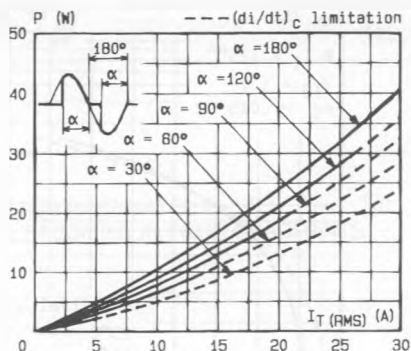


Fig.1 - Maximum mean power dissipation versus RMS on-state current ($F = 60$ Hz).

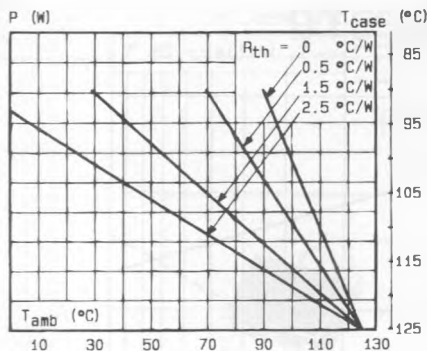


Fig.2 - Correlation between maximum mean power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact.

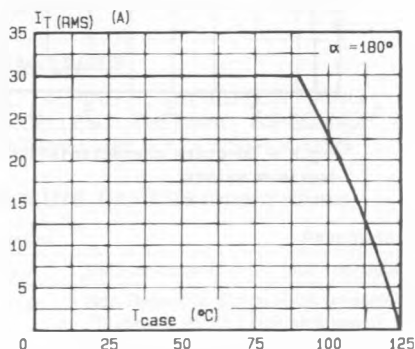


Fig.3 - RMS on-state current versus case temperature.

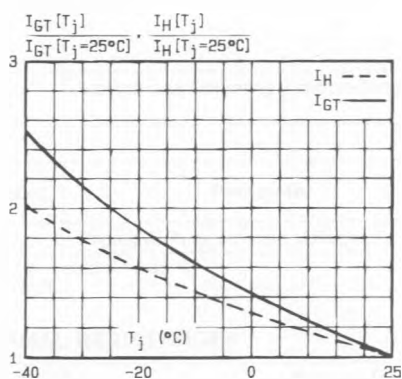


Fig.5 - Relative variation of gate trigger current and holding current versus junction temperature.

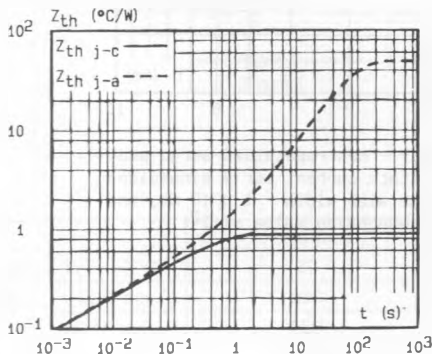


Fig.4 - Thermal transient impedance junction to case and junction to ambient versus pulse duration.

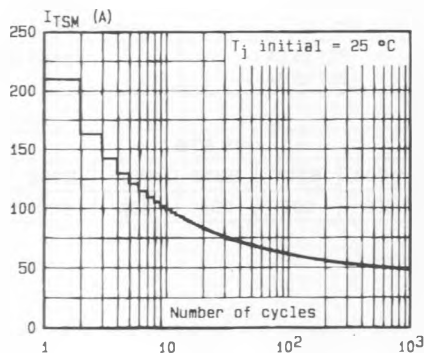


Fig.6 - Non repetitive surge peak on-state current versus number of cycles.

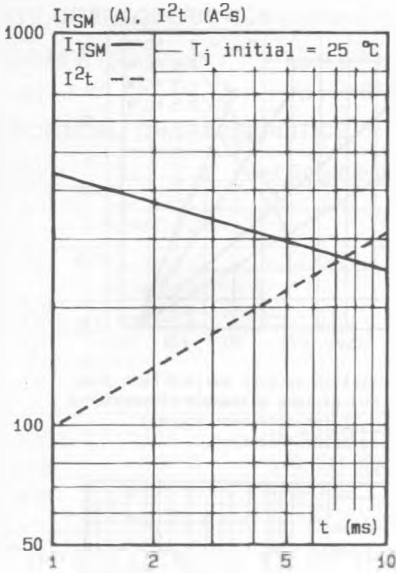


Fig.7 - Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t \leq 10$ ms, and corresponding value of I^2t .

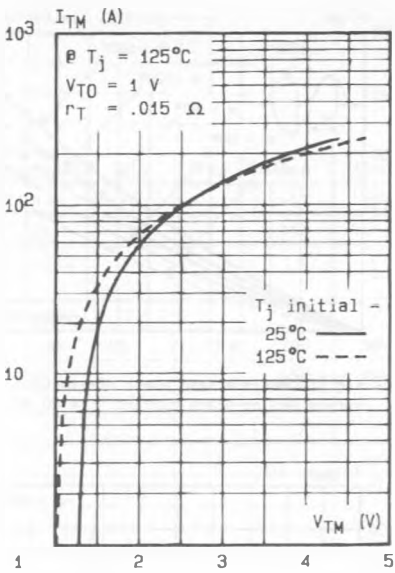


Fig.8 - On-state characteristics (maximum values).